

This Page Is Inserted by IFW Operations
and is not a part of the Official Record

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
- TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

IMAGES ARE BEST AVAILABLE COPY.

**As rescanning documents *will not* correct images,
please do not report the images to the
Image Problem Mailbox.**

The Delphion Integrated View

Buy Now: [PDF](#) | [More choices...](#)

Tools: Add to Work File: [Create new](#)

View: [INPADOC](#) | Jump to: [Top](#) Go to: [Derwent...](#)

Title: **JP5819777A2: SEMICONDUCTOR NONVOLATILE MEMORY STORAGE**

Country: **JP Japan**

Kind: **A**

Inventor: **MATSUO RYUICHI;**

Assignee: **MITSUBISHI ELECTRIC CORP**
[News, Profiles, Stocks and More about this company](#)

Published / Filed: **1983-11-17 / 1982-05-12**

Application
Number: **JP1982000082006**

IPC Code: **H01L 29/78; G11C 11/40; H01L 27/10;**

Priority Number: **1982-05-12 JP1982000082006**

Abstract:

PURPOSE: To provide the memory region with which information can be stored even when ultraviolet rays are irradiated by a method wherein an ultraviolet ray type FET for nonvolatile memory, having a floating gate and a control gate, is arranged in matrix form, and at least one of the above is covered by an ultraviolet ray shielding film.

CONSTITUTION: An N type source 2 and a drain 3 are provided on a P type Si substrate 1, a floating gate 4 and a control gate are provided and an FAMOS type FET of N-channel is arranged in matrix form as a memory element. At least one of them is covered by an Al film 8 and prevent the infiltration of ultraviolet ray 7 using it. As a result, the information once written-in can be maintained at this part even when ultraviolet rays are irradiated. Accordingly, the established information is memorized in this region, thereby enabling to prevent the elimination of information by the ultraviolet rays irradiated after an unexpected writing-in or the rewriting of other sections have been performed.

COPYRIGHT: (C)1983,JPO&Japio

INPADOC Legal Status: **None** Buy Now: [Family Legal Status Report](#)
Family: [Show 2 known family members](#)

Forward
References: **Go to Result Set: Forward references (3)**

Buy PDF	Patent	Pub.Date	Inventor	Assignee	Title
	US5070378	1991-12-03	Yamagata; Yasushi	NEC Corporation	EPROM erasable by UV radiation redundant circuit
	US4942450	1990-07-17	Iwashita; Shinichi	NEC Corporation	Semiconductor memory device hav volatile memory transistors
	US4758984	1988-07-19	Yoshida; Masanobu	Fujitsu Limited	Semiconductor memory device incl read only memory element for stori information